CLAIMS

What is claimed is:

1. A method of forming a semiconductor device assembly, said method comprising:
providing a substrate having an upper surface and a lower surface;
depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;
patterning the layer of copper on one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;
depositing at least one layer of metal on at least a portion of the layer of copper; and
connecting one end of a conductor lead of a TAB tape to the at least one layer of metal.

2. The method of claim 1, further comprising:
connecting one end of conductor lead of a TAB tape to the at least one layer of gold metal using a wire bond.

3. A method of forming a semiconductor device assembly, said method comprising:
providing a substrate having an upper surface and a lower surface;
depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;
patterning the layer of copper on one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;
depositing at least one layer of gold metal on at least a portion of the layer of copper; and
connecting one end of a conductor lead of a TAB tape to the at least one layer of gold metal.

4. A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising:
depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;

patterning the layer of copper on one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of metal on at least a portion of the layer of copper; and

connecting one end of a conductor lead of a TAB tape to the at least one layer of metal.

5. The method of claim 4, further comprising:

connecting one end of conductor lead of a TAB tape to the at least one layer of gold metal using a wire bond.

6. A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising:

depositing a layer of copper on one surface of the upper surface and the lower surface of the substrate;

patterning the layer of copper on one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of gold metal on at least a portion of the layer of copper; and

connecting one end of a conductor lead of a TAB tape to the at least one layer of gold metal.